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Vishay Siliconix

## Automotive N-Channel 30 V (D-S) 175 °C MOSFET



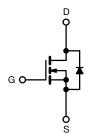
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.00077				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.00128				
I <sub>D</sub> (A)	410				
Configuration	Single				
Package	PowerPAK SO-8L				

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Q<sub>gd</sub>/Q<sub>gs</sub> ratio < 1 optimizes switching characteristics</li>







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	(T <sub>C</sub> = 25 °C, unles	s otherwise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	30	V	
Gate-source voltage		$V_{GS}$	± 20	V	
Continuous drain current	T <sub>C</sub> = 25 °C	1	410		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	331		
Continuous source current (diode conduction)		I <sub>S</sub>	454	Α	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	410		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	55.5		
Single pulse avalanche energy	L = 0.1 IIII1	E <sub>AS</sub>	154	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	500	W	
waxiinum power dissipation 4	T <sub>C</sub> = 125 °C	$P_{D}$	166	VV	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) <sup>c</sup>			260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	$R_{thJA}$	42	°C/W
Junction-to-case (drain)		$R_{thJC}$	0.3	C/VV

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	vise noted) TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				L			
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	30	-	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$		1.5	2.0	2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A	-	0.00066	0.00077	
Duning any unitarity and a state and a state and a		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.00130	0
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.00150	Ω
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	0.0010	0.00128	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	55	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	6984	9778	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	1774	2484	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	186	261	
Total gate charge <sup>c</sup>	Qg			-	129	195	
Gate-source charge c	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 15 \text{ A}$	-	22	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	25	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz		0.8	1.7	2.6	Ω
Turn-on delay time c	t <sub>d(on)</sub>			-	15	23	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$V_{DD} = 15 \text{ V}, R_{I} = 1.0 \Omega$		18	29	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 15 A$ ,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	55	83	ns
Fall time <sup>c</sup>	t <sub>f</sub>	1		-	19	29	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	1816	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	15 A, V <sub>GS</sub> = 0 V	-	-	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>			-	58	116	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs		-	71	142	nC
Reverse recovery fall time	t <sub>a</sub>			-	29	-	
Reverse recovery rise time	t <sub>b</sub>	7		-	30	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-2.2	-	Α

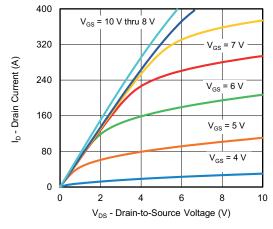
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

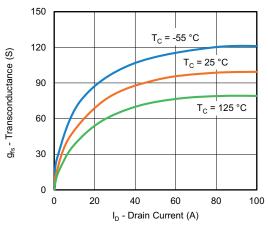
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



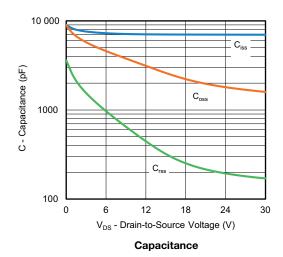
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

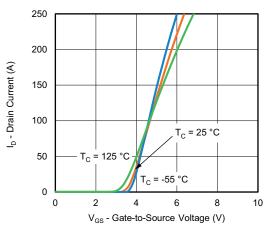


#### **Output Characteristics**

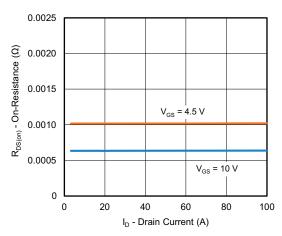


Transconductance

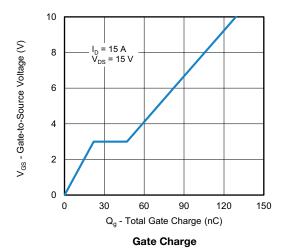




**Transfer Characteristics** 

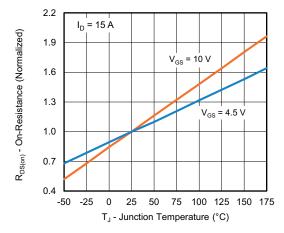


**On-Resistance vs. Drain Current** 

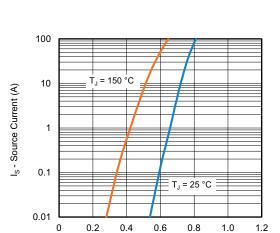




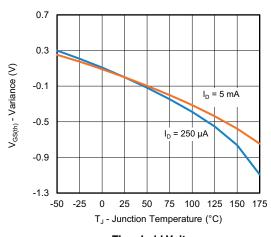
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



V<sub>SD</sub> - Source-to-Drain Voltage (V) **Source Drain Diode Forward Voltage** 

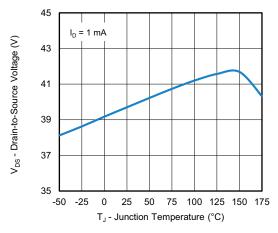


**Threshold Voltage** 

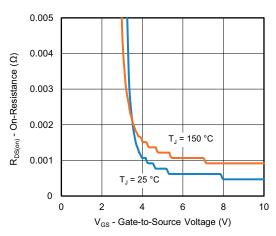


Note

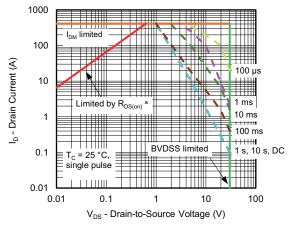
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**Drain Source Breakdown vs. Junction Temperature** 



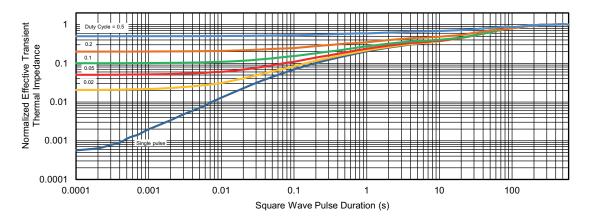
On-Resistance vs. Gate-to Source Voltage



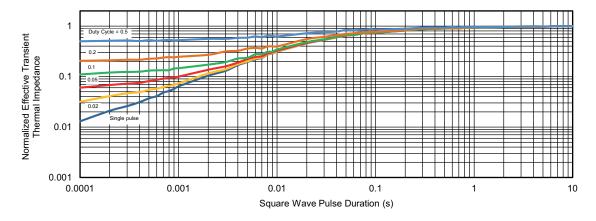
Safe Operating Area

For technical questions, contact: automostechsupport@vishay

### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

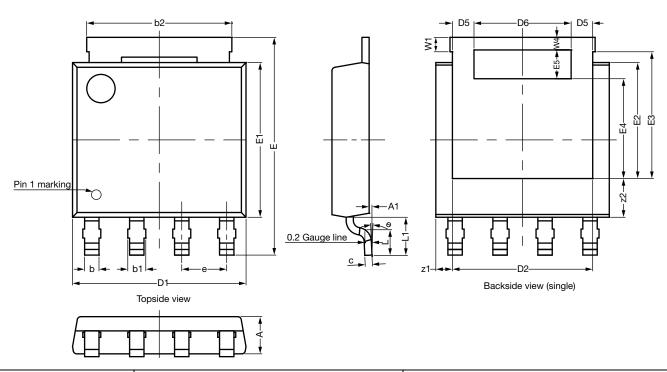
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?78994.



# PowerPAK® SO-8L (PPKSO8LWLA) Case Outline 3



DIM.		MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	1.00	1.05	1.10	0.039	0.041	0.043		
A1	0.00		0.127	0.000		0.005		
b	0.33	0.41	0.49	0.013	0.016	0.019		
b1	0.43	0.51	0.59	0.017	0.020	0.023		
b2	4.00	4.10	4.20	0.157	0.161	0.165		
С	0.15	0.20	0.25	0.006	0.008	0.010		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D5	0.51	0.61	0.71	0.020	0.024	0.028		
D6	2.64	2.74	2.84	0.104	0.108	0.112		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	3.18	3.28	3.38	0.125	0.129	0.133		
E3	3.48	3.58	3.68	0.137	0.141	0.145		
E4	2.72	2.82	2.92	0.107	0.111	0.115		
E5	0.71	0.81	0.91	0.028	0.032	0.036		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
W1	0.31	0.41	0.51	0.012	0.016	0.020		
W4	0.31	0.36	0.41	0.012	0.014	0.016		
z1	0.37	0.47	0.57	0.015	0.019	0.022		
z2	0.99	1.09	1.19	0.039	0.043	0.047		
θ	0°		5°	0°		5°		

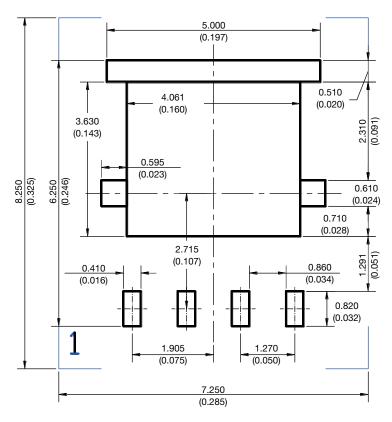
#### Note

• Millimeter will govern

Revison: 18-Sep-2023 1 Document Number: 76666



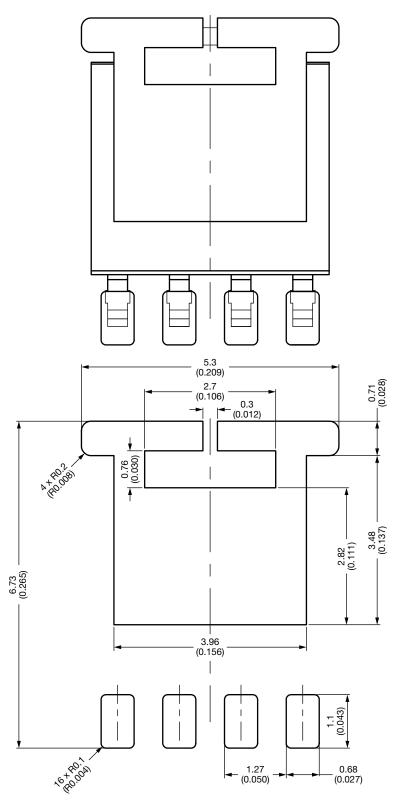
#### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



# Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)



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